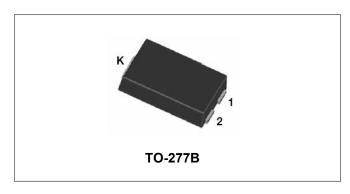


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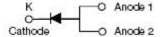
# **MBR1060S SCHOTTKY RECTIFIER**



#### **Features**

- Designed as Bypass Diodes for Solar Panels
- High Forward Surge Capability
- Ultra Low Forward Voltage Drop
- Excellent High Temperature Stability
- This is a Halogen Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



## **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

#### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ \end{array}$	-	60	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=80°C, rectangular wave form	10	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, Tc=25°C	200	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop *	$V_{F1}$	@ 10A, Pulse, T <sub>J</sub> = 25 °C	-	0.63	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25  ^{\circ}\text{C}$	-	1.0	mA
Junction Capacitance	Cj	@V <sub>R</sub> = 5.0 V, Tc=25 °C f <sub>SIG</sub> = 1MHz	-	850	pF

 $<sup>^*</sup>$  Pulse width < 300  $\mu$ s, duty cycle < 2%



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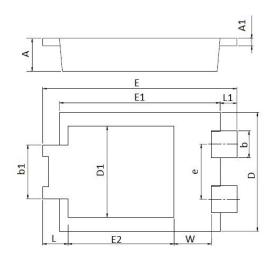




## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>0</sub> JC	DC operation	6.0	°C/W
Typical Thermal Resistance Junction to Soldering Point	$R_{ heta JS}$	DC operation	1.5	°C/W
Approximate Weight	wt	-	0.08	g

#### **Mechanical Dimensions TO-277B**





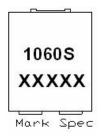
SYMBOL	Millimeters		Inches		
STWIDOL	Min.	Max.	Min.	Max.	
Α	0.95	1.25	0.037	0.049	
A1	0.20	0.30	0.008	0.012	
b	0.85	0.95	0.033	0.037	
b1	1.70	1.90	0.067	0.075	
D	3.88	4.08	0.153	0.161	
D1	2.90	3.20	0.114	0.126	
е	1.74	1.94	0.069	0.076	
E	6.30	6.70	0.248	0.264	
E1	5.28	5.48	0.208	0.216	
E2	3.40	3.70	0.134	0.146	
L	0.70	1.00	0.028	0.039	
L1	0.41	0.71	0.016	0.028	
W	1.10	1.40	0.043	0.055	

# **Ordering Information**

Device	Package	Shipping	
MBR1060S	TO-277B(Pb-Free)	5000pcs/ reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



Where XXXXX is YYWWL

10 = Forward Current (10A) 60 = Reverse Voltage (60V) = Package type = Year WW = Week = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

<sup>•</sup> China - Germany - Korea - Singapore - United States •

<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •

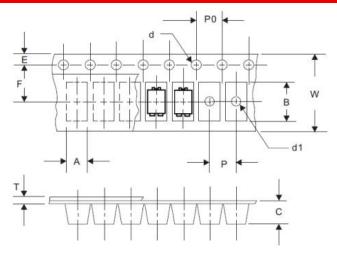


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#### Carrier Tape Specification TO-277B



SYMBOL	Millimeters		
STWBOL	Min.	Max.	
Α	4.28	4.48	
В	6.80	7.10	
С	1.30	1.50	
d	1.40	1.60	
d1	-	1.50	
E	1.65	1.85	
F	5.40	5.60	
Р	7.90	8.10	
P0	3.90	4.10	
Т	0.24	0.44	
W	11.70	12.30	

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